

KEC

SEMICONDUCTOR
TECHNICAL DATA

KTA1725

EPITAXIAL PLANAR PNP TRANSISTOR

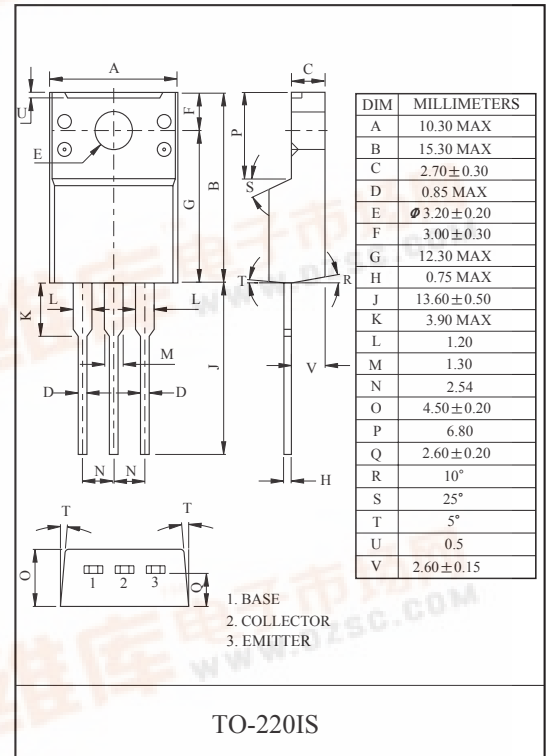
HIGH POWER AMPLIFIER APPLICATION.

FEATURES

- Complementary to KTC4511.

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-6	A
Base Current	I_B	-3	A
Collector Power Dissipation (Tc=25℃)	P_C	30	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~ 150	℃

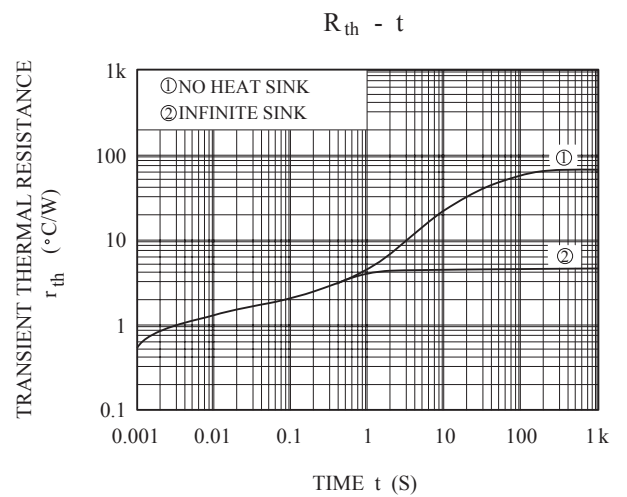
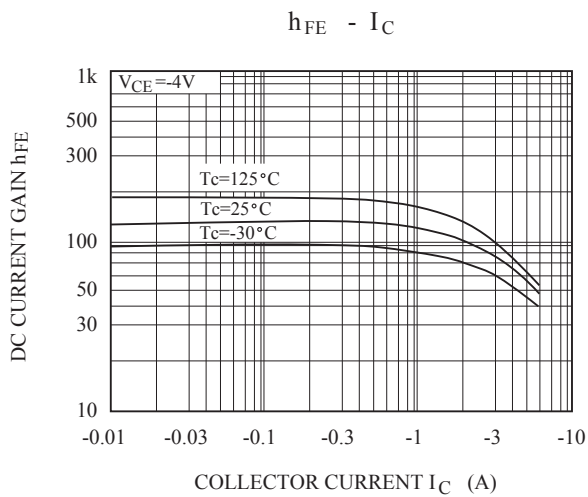
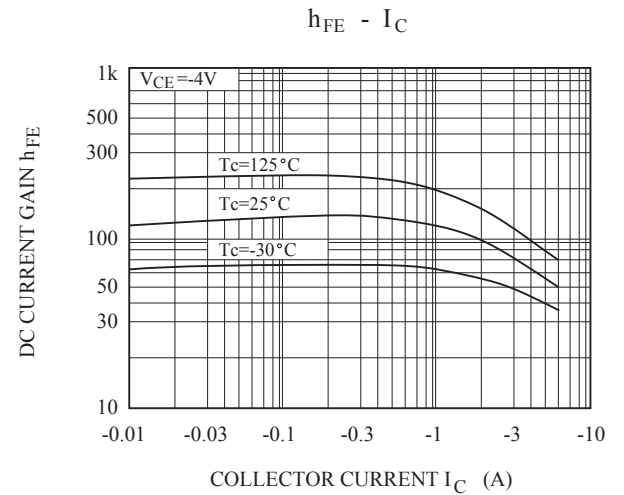
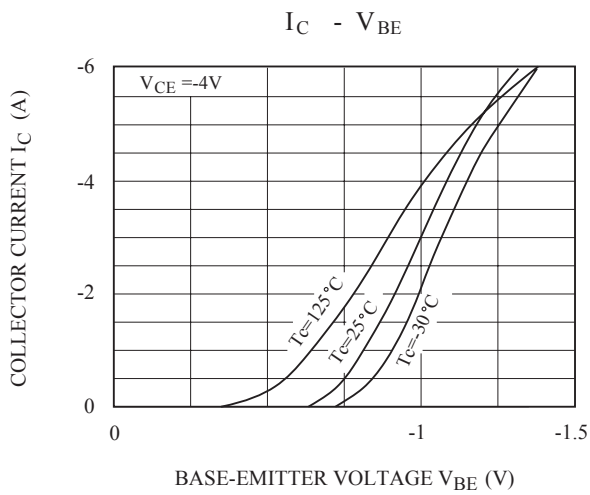
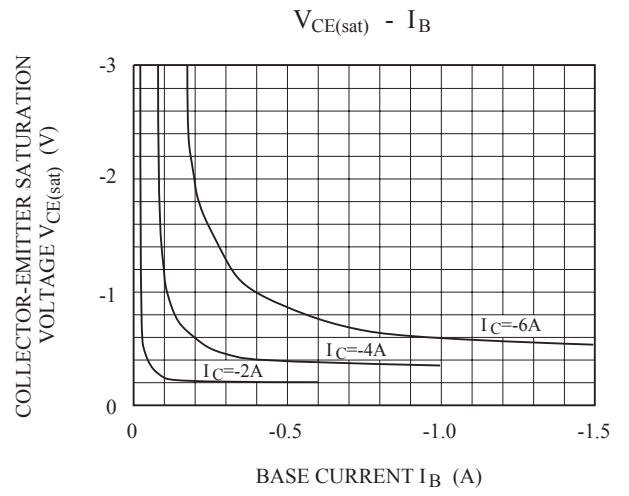
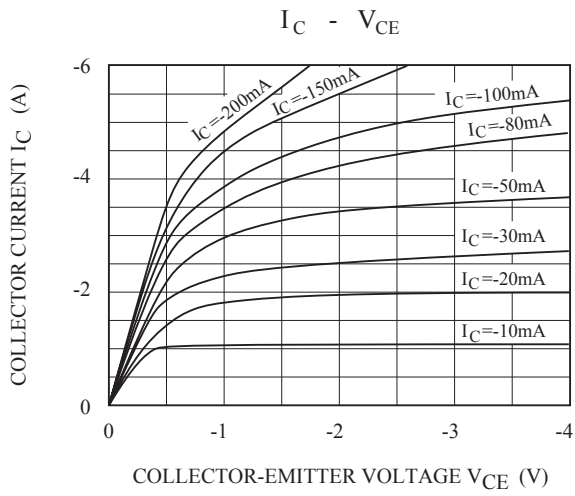


ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-80V, I_E=0$	-	-	-10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-6V, I_C=0$	-	-	-10	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-25mA, I_B=0$	-80	-	-	V
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=-4V, I_C=-2A$	55	-	160	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$	-	-	-0.5	V
Transition Frequency	f_T	$V_{CE}=-12V, I_C=-0.5A$	-	20	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	150	-	pF

Note : h_{FE} Classification R:55~110, O:80~160.

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